

Attorney Docket No. 5308-286

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sumakeris et al.

Serial No.: 10/686,795

Filed: October 16, 2003

For: METHOD OF FORMING POWER SEMICONDUCTOR DEVICES USING BOULE-GROWN SILICON CARBIDE DRIFT LAYERS AND POWER SEMICONDUCTOR DEVICES FORMED THEREBY

Group Art Unit: 2811

Examiner: Cuong Quang Nguyen

Confirmation No.: 7928

Date: January 20, 2005

Mail Stop Amendment

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

FOURTH SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a Supplemental Form PTO-1449 listing documents cited in the International Search Report, that were not previously cited in an Information Disclosure Statement, for corresponding International Application Number PCT/US2004/31883. Each document listed on the attached PTO-1449 was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. A copy of any listed foreign patent document and/or non-patent literature including the Search Report, is enclosed. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the amendment by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(ii) effective October 21, 2004.

No fee is believed due; however, the Commissioner is hereby authorized to charge any deficiency or credit any refund to Deposit Account No. 50-0220.

Respectfully submitted,


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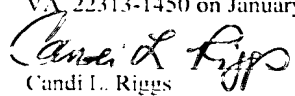
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Candi L. Riggs

Sheet E1

Application Number	10/686,795
Filing Date	October 16, 2003
First Named Inventor	Joseph J. Sumakeris
Group Art Unit	2811
Examiner Name	Cuong Quang Nguyen
Attorney Docket Number	5308-248

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OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	4	Baranov et al., "EPR Study of Shallow and Deep Phosphorous Centers in 6H-SiC," Physical Review B66, 2002, pp. 165206-1 through 165206-7	
	5	Rashid et al., "Trench Oxide Protection for 10 kV 4H-SiC Trench MOSFETs," Power Electronics and Drive Systems, 2003, Vol. 2, pp. 1354-1358	
	6	Sugawara et al., "12-19kV 4H-SiC pin Diodes with Low Power Loss," Proceedings of 2001 International Symposium on Power Semiconductor Devices & Ics, Osaka, pp. 27-30	
	7	Notification of Transmittal of the International Search Report and the Written Opinion of the International Searching Authority, or the Declaration, PCT/US2004/031883, January 7, 2005	

Date Considered _____

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.